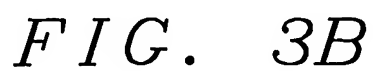
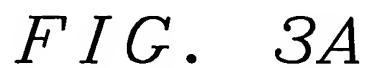


A cross-sectional view of a semiconductor device. The device consists of a substrate with a series of alternating regions. The regions are labeled from left to right: 10 (ANODE), 16 (CATHODE), 18 (ANODE), 20 (CATHODE), and 22 (ANODE). Each region contains a vertical stack of three squares, representing a stack of semiconductor layers. The regions are separated by dashed vertical lines. The regions are labeled 12A, 12B, 12C, 12D, and 12E at the bottom. The regions 10, 16, 18, 20, and 22 are labeled at the top. The regions 10, 16, 18, 20, and 22 are labeled as ANODE, CATHODE, ANODE, CATHODE, and ANODE respectively.

FIG. 1C – Prior Art



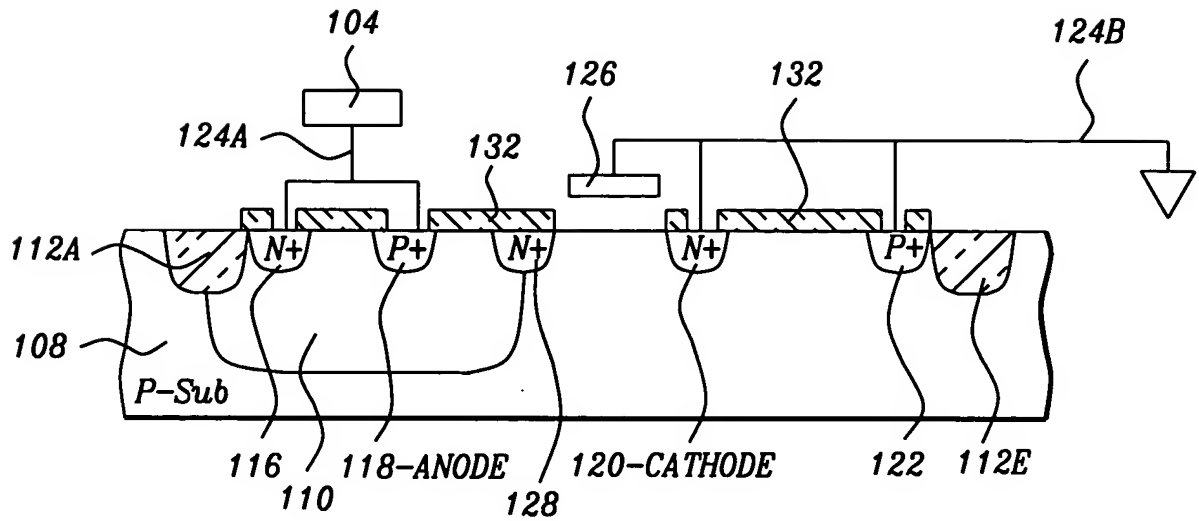


FIG. 4

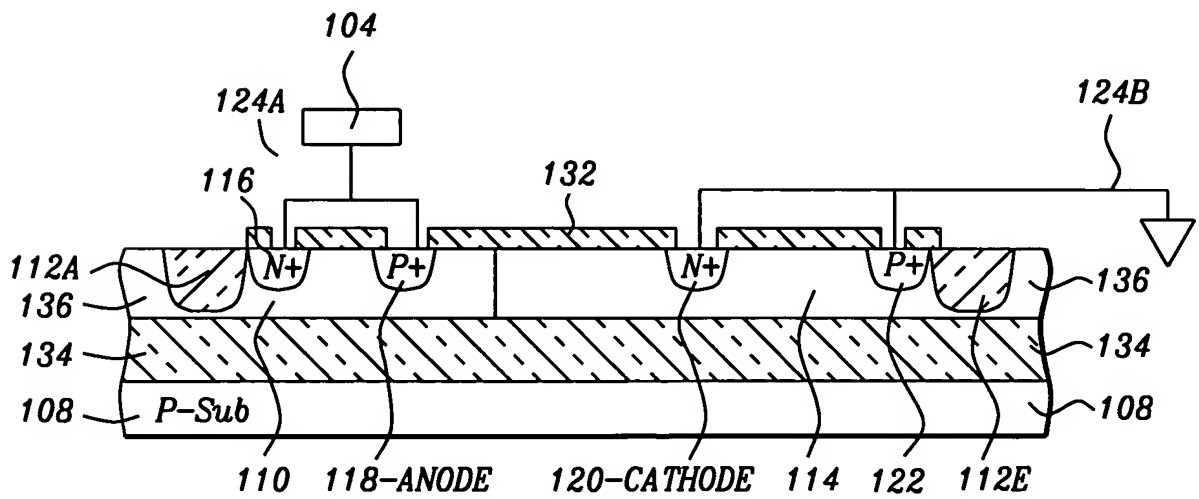


FIG. 5

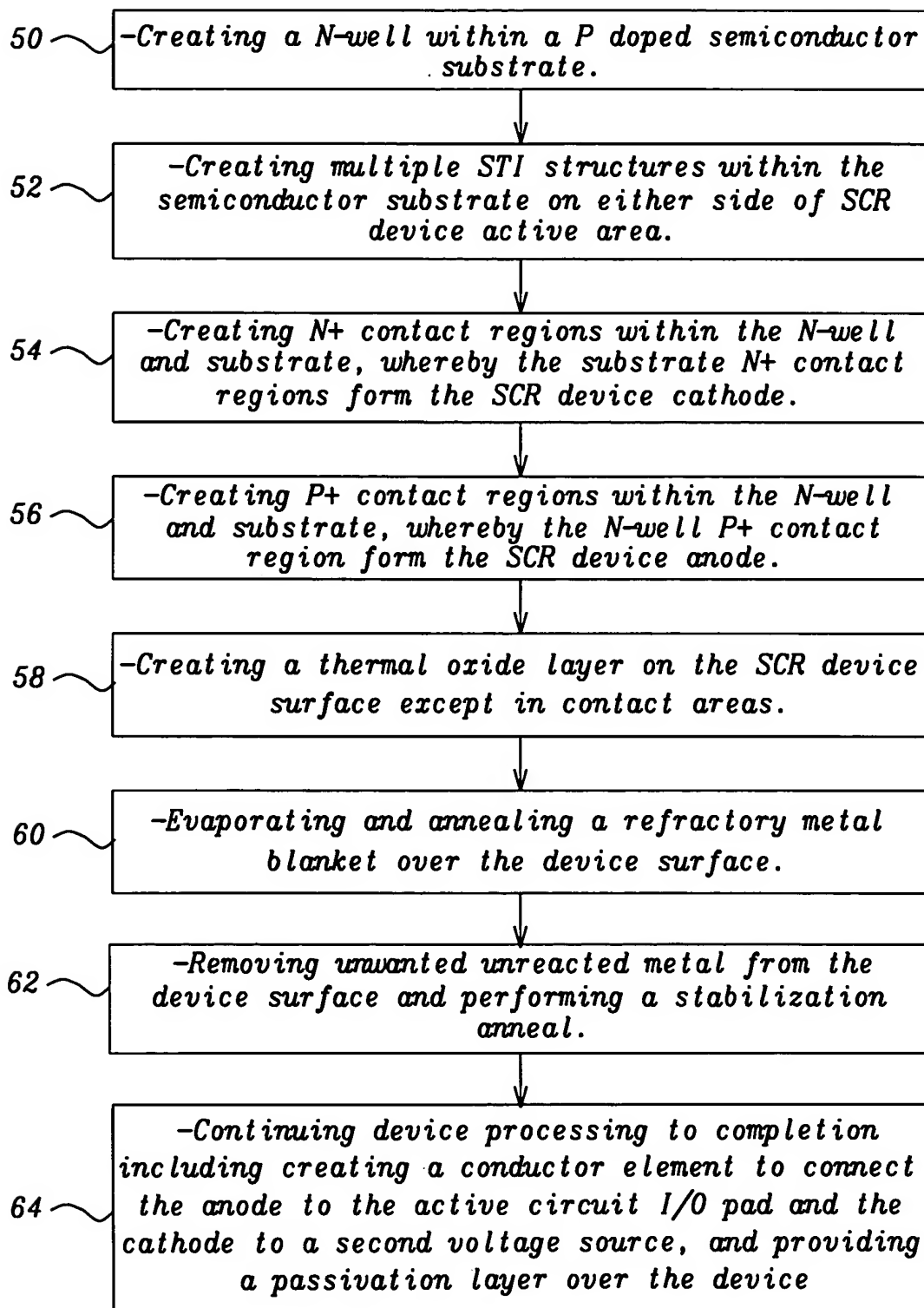


FIG. 6